

# 74HC3G04; 74HCT3G04

## Inverter

Rev. 03 — 2 July 2008

Product data sheet

## 1. General description

The 74HC3G04 and 74HCT3G04 are high-speed Si-gate CMOS devices. They provide three inverting buffers.

The HC device has CMOS input switching levels and supply voltage range 2 V to 6 V.

The HCT device has TTL input switching levels and supply voltage range 4.5 V to 5.5 V.

## 2. Features

- Wide supply voltage range from 2.0 V to 6.0 V
- Symmetrical output impedance
- High noise immunity
- Low power dissipation
- Balanced propagation delays
- Multiple package options
- ESD protection:
  - ◆ HBM JESD22-A114E exceeds 2000 V
  - ◆ MM JESD22-A115-A exceeds 200 V
- Specified from  $-40\text{ }^{\circ}\text{C}$  to  $+85\text{ }^{\circ}\text{C}$  and  $-40\text{ }^{\circ}\text{C}$  to  $+125\text{ }^{\circ}\text{C}$

## 3. Ordering information

Table 1. Ordering information

Type number	Package			
	Temperature range	Name	Description	Version
74HC3G04DP 74HCT3G04DP	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	TSSOP8	plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm	SOT505-2
74HC3G04DC 74HCT3G04DC	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	VSSOP8	plastic very thin shrink small outline package; 8 leads; body width 2.3 mm	SOT765-1
74HC3G04GD 74HCT3G04GD	$-40\text{ }^{\circ}\text{C}$ to $+125\text{ }^{\circ}\text{C}$	XSON8U	plastic extremely thin small outline package; no leads; 8 terminals; UTLP based; body $3 \times 2 \times 0.5$ mm	SOT996-2

## 4. Marking

Table 2. Marking codes

Type number	Marking code
74HC3G04DP	H04
74HCT3G04DP	T04
74HC3G04DC	H04
74HCT3G04DC	T04
74HC3G04GD	H04
74HCT3G04GD	T04

## 5. Functional diagram

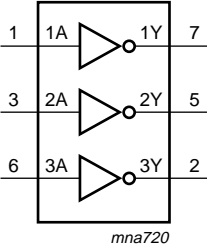


Fig 1. Logic symbol

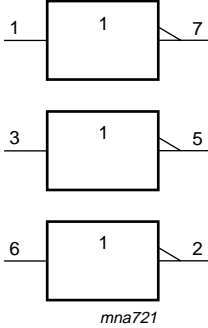


Fig 2. IEC logic symbol

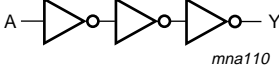


Fig 3. Logic diagram (one gate)

## 6. Pinning information

### 6.1 Pinning

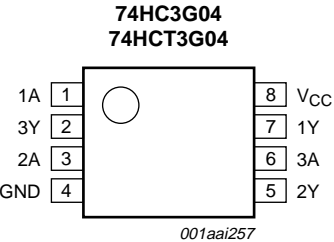


Fig 4. Pin configuration SOT505-2 (TSSOP8) and SOT765-1 (VSSOP8)

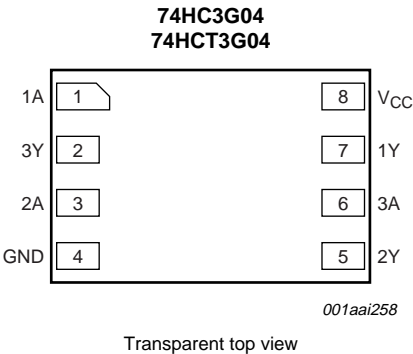


Fig 5. Pin configuration SOT996-2 (XSON8U)

## 6.2 Pin description

**Table 3.** Pin description

Symbol	Pin	Description
1A, 2A, 3A	1, 3, 6	data input
GND	4	ground (0 V)
1Y, 2Y, 3Y	7, 5, 2	data output
V <sub>CC</sub>	8	supply voltage

## 7. Functional description

**Table 4.** Function table<sup>[1]</sup>

Input	Output
nA	nY
L	H
H	L

[1] H = HIGH voltage level; L = LOW voltage level.

## 8. Limiting values

**Table 5.** Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134). Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>CC</sub>	supply voltage		-0.5	+7.0	V
I <sub>IK</sub>	input clamping current	V <sub>I</sub> < -0.5 V or V <sub>I</sub> > V <sub>CC</sub> + 0.5 V	[1] -	±20	mA
I <sub>OK</sub>	output clamping current	V <sub>O</sub> < -0.5 V or V <sub>O</sub> > V <sub>CC</sub> + 0.5 V	[1] -	±20	mA
I <sub>O</sub>	output current	V <sub>O</sub> = -0.5 V to (V <sub>CC</sub> + 0.5 V)	[1] -	25	mA
I <sub>CC</sub>	supply current		[1] -	50	mA
I <sub>GND</sub>	ground current		[1] -50	-	mA
T <sub>stg</sub>	storage temperature		-65	+150	°C
P <sub>D</sub>	dynamic power dissipation	T <sub>amb</sub> = -40 °C to +125 °C	[2] -	300	mW

[1] The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

[2] For TSSOP8 package: above 55 °C the value of P<sub>tot</sub> derates linearly with 2.5 mW/K.  
 For VSSOP8 package: above 110 °C the value of P<sub>tot</sub> derates linearly with 8 mW/K.  
 For XSON8 package: above 45 °C the value of P<sub>tot</sub> derates linearly with 2.4 mW/K.

## 9. Recommended operating conditions

**Table 6. Recommended operating conditions**

Voltages are referenced to GND (ground = 0 V).

Symbol	Parameter	Conditions	74HC3G04			74HCT3G04			Unit
			Min	Typ	Max	Min	Typ	Max	
V <sub>CC</sub>	supply voltage		2.0	5.0	6.0	4.5	5.0	5.5	V
V <sub>I</sub>	input voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
V <sub>O</sub>	output voltage		0	-	V <sub>CC</sub>	0	-	V <sub>CC</sub>	V
T <sub>amb</sub>	ambient temperature		-40	+25	+125	-40	+25	+125	°C
Δt/ΔV	input transition rise and fall rate	V <sub>CC</sub> = 2.0 V	-	-	625	-	-	-	ns/V
		V <sub>CC</sub> = 4.5 V	-	1.67	139	-	1.67	139	ns/V
		V <sub>CC</sub> = 6.0 V	-	-	83	-	-	-	ns/V

## 10. Static characteristics

**Table 7. Static characteristics**

Voltages are referenced to GND (ground = 0 V). All typical values are measured at T<sub>amb</sub> = 25 °C.

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
<b>74HC3G04</b>										
V <sub>IH</sub>	HIGH-level input voltage	V <sub>CC</sub> = 2.0 V	1.5	1.2	-	1.5	-	1.5	-	V
		V <sub>CC</sub> = 4.5 V	3.15	2.4	-	3.15	-	3.15	-	V
		V <sub>CC</sub> = 6.0 V	4.2	3.2	-	4.2	-	4.2	-	V
V <sub>IL</sub>	LOW-level input voltage	V <sub>CC</sub> = 2.0 V	-	0.8	0.5	-	0.5	-	0.5	V
		V <sub>CC</sub> = 4.5 V	-	2.1	1.35	-	1.35	-	1.35	V
		V <sub>CC</sub> = 6.0 V	-	2.8	1.8	-	1.8	-	1.8	V
V <sub>OH</sub>	HIGH-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 2.0 V	1.9	2.0	-	1.9	-	1.9	-	V
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 4.5 V	4.4	4.5	-	4.4	-	4.4	-	V
		I <sub>O</sub> = -20 μA; V <sub>CC</sub> = 6.0 V	5.9	6.0	-	5.9	-	5.9	-	V
		I <sub>O</sub> = -4.0 mA; V <sub>CC</sub> = 4.5 V	4.18	4.32	-	4.13	-	3.7	-	V
	I <sub>O</sub> = -5.2 mA; V <sub>CC</sub> = 6.0 V	5.63	5.81	-	5.63	-	5.2	-	V	
V <sub>OL</sub>	LOW-level output voltage	V <sub>I</sub> = V <sub>IH</sub> or V <sub>IL</sub>								
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 2.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 4.5 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 20 μA; V <sub>CC</sub> = 6.0 V	-	0	0.1	-	0.1	-	0.1	V
		I <sub>O</sub> = 4.0 mA; V <sub>CC</sub> = 4.5 V	-	0.15	0.26	-	0.33	-	0.4	V
	I <sub>O</sub> = 5.2 mA; V <sub>CC</sub> = 6.0 V	-	0.16	0.26	-	0.33	-	0.4	V	
I <sub>I</sub>	input leakage current	V <sub>I</sub> = V <sub>CC</sub> or GND; V <sub>CC</sub> = 6.0 V	-	-	±0.1	-	±1.0	-	±1.0	μA
I <sub>CC</sub>	supply current	per input pin; V <sub>CC</sub> = 6.0 V; V <sub>I</sub> = V <sub>CC</sub> or GND; I <sub>O</sub> = 0 A;	-	-	1.0	-	10	-	20	μA

**Table 7. Static characteristics ...continued**

*Voltages are referenced to GND (ground = 0 V). All typical values are measured at  $T_{amb} = 25\text{ }^{\circ}\text{C}$ .*

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
$C_I$	input capacitance		-	1.5	-	-	-	-	-	pF
<b>74HCT3G04</b>										
$V_{IH}$	HIGH-level input voltage	$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	2.0	1.6	-	2.0	-	2.0	-	V
$V_{IL}$	LOW-level input voltage	$V_{CC} = 4.5\text{ V to }5.5\text{ V}$	-	1.2	0.8	-	0.8	-	0.8	V
$V_{OH}$	HIGH-level output voltage	$V_I = V_{IH}$ or $V_{IL}$								
		$I_O = -20\text{ }\mu\text{A}; V_{CC} = 4.5\text{ V}$	4.4	4.5	-	4.4	-	4.4	-	V
		$I_O = -4.0\text{ mA}; V_{CC} = 4.5\text{ V}$	4.18	4.32	-	4.13	-	3.7	-	V
$V_{OL}$	LOW-level output voltage	$V_I = V_{IH}$ or $V_{IL}$								
		$I_O = 20\text{ }\mu\text{A}; V_{CC} = 4.5\text{ V}$	-	0	0.1	-	0.1	-	0.1	V
		$I_O = 4.0\text{ mA}; V_{CC} = 4.5\text{ V}$	-	0.15	0.26	-	0.33	-	0.4	V
$I_I$	input leakage current	$V_I = V_{CC}$ or GND; $V_{CC} = 5.5\text{ V}$	-	-	$\pm 0.1$	-	$\pm 1.0$	-	$\pm 1.0$	$\mu\text{A}$
$I_{CC}$	supply current	per input pin; $V_{CC} = 5.5\text{ V}; V_I = V_{CC}$ or GND; $I_O = 0\text{ A}$ ;	-	-	1.0	-	10	-	20	$\mu\text{A}$
$\Delta I_{CC}$	additional supply current	per input; $V_{CC} = 4.5\text{ V to }5.5\text{ V}; V_I = V_{CC} - 2.1\text{ V}; I_O = 0\text{ A}$	-	-	300	-	375	-	410	$\mu\text{A}$
$C_I$	input capacitance		-	1.5	-	-	-	-	-	pF

## 11. Dynamic characteristics

**Table 8. Dynamic characteristics**

*Voltages are referenced to GND (ground = 0 V); all typical values are measured at  $T_{amb} = 25\text{ }^{\circ}\text{C}$ ; for test circuit see [Figure 7](#).*

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
<b>74HC3G04</b>										
$t_{pd}$	propagation delay	nA to nY; see <a href="#">Figure 6</a> <sup>[1]</sup>								
		$V_{CC} = 2.0\text{ V}$	-	22	75	-	90	-	110	ns
		$V_{CC} = 4.5\text{ V}$	-	8	15	-	18	-	22	ns
		$V_{CC} = 6.0\text{ V}$	-	6	13	-	16	-	20	ns
$t_t$	transition time	see <a href="#">Figure 6</a> <sup>[2]</sup>								
		$V_{CC} = 2.0\text{ V}$	-	18	75	-	95	-	125	ns
		$V_{CC} = 4.5\text{ V}$	-	6	15	-	19	-	25	ns
		$V_{CC} = 6.0\text{ V}$	-	5	13	-	16	-	20	ns
$C_{PD}$	power dissipation capacitance	$V_I = \text{GND to } V_{CC}$ <sup>[3]</sup>	-	9	-	-	-	-	-	pF

**Table 8. Dynamic characteristics ...continued**

Voltages are referenced to GND (ground = 0 V); all typical values are measured at  $T_{amb} = 25\text{ }^\circ\text{C}$ ; for test circuit see [Figure 7](#).

Symbol	Parameter	Conditions	25 °C			-40 °C to +85 °C		-40 °C to +125 °C		Unit
			Min	Typ	Max	Min	Max	Min	Max	
<b>74HCT3G04</b>										
$t_{pd}$	propagation delay	nA to nY; see <a href="#">Figure 6</a> [1] $V_{CC} = 4.5\text{ V}$	-	10	18	-	23	-	29	ns
$t_t$	transition time	$V_{CC} = 4.5\text{ V}$ ; see <a href="#">Figure 6</a> [2]	-	6	15	-	19	-	22	ns
$C_{PD}$	power dissipation capacitance	$V_I = \text{GND to } V_{CC} - 1.5\text{ V}$ [3]	-	9	-	-	-	-	-	pF

[1]  $t_{pd}$  is the same as  $t_{PLH}$  and  $t_{PHL}$ .

[2]  $t_t$  is the same as  $t_{TLH}$  and  $t_{THL}$ .

[3]  $C_{PD}$  is used to determine the dynamic power dissipation ( $P_D$  in  $\mu\text{W}$ ).

$$P_D = C_{PD} \times V_{CC}^2 \times f_i \times N + \Sigma(C_L \times V_{CC}^2 \times f_o) \text{ where:}$$

$f_i$  = input frequency in MHz;

$f_o$  = output frequency in MHz;

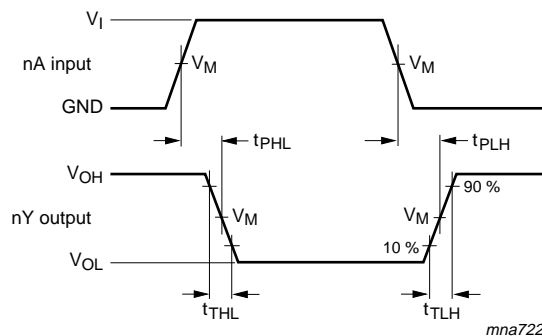
$C_L$  = output load capacitance in pF;

$V_{CC}$  = supply voltage in V;

$N$  = number of inputs switching;

$\Sigma(C_L \times V_{CC}^2 \times f_o)$  = sum of outputs.

## 12. Waveforms



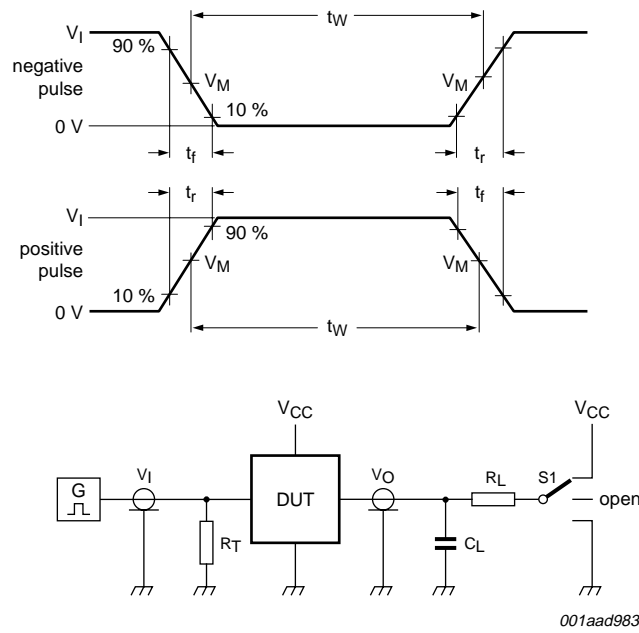
Measurement points are given in [Table 9](#).

Logic levels:  $V_{OL}$  and  $V_{OH}$  are typical output voltage levels that occur with the output load.

**Fig 6. The data input (nA) to output (nY) propagation delays**

**Table 9. Measurement points**

Type	Input	Output
	$V_M$	$V_M$
74HC3G04	$0.5 \times V_{CC}$	$0.5 \times V_{CC}$
74HCT3G04	1.3 V	1.3 V



Test data is given in [Table 10](#).

Definitions for test circuit:

$R_T$  = Termination resistance should be equal to output impedance  $Z_o$  of the pulse generator.

$C_L$  = Load capacitance including jig and probe capacitance.

$R_L$  = Load resistance.

S1 = Test selection switch.

**Fig 7. Load circuit for measuring switching times**

**Table 10. Test data**

Type	Input		Load		S1 position
	$V_I$	$t_r, t_f$	$C_L$	$R_L$	$t_{PHL}, t_{PLH}$
74HC3G04	$V_{CC}$	$\leq 6$ ns	50 pF	1 k $\Omega$	open
74HCT3G04	3 V	$\leq 6$ ns	50 pF	1 k $\Omega$	open

13. Package outline

TSSOP8: plastic thin shrink small outline package; 8 leads; body width 3 mm; lead length 0.5 mm SOT505-2

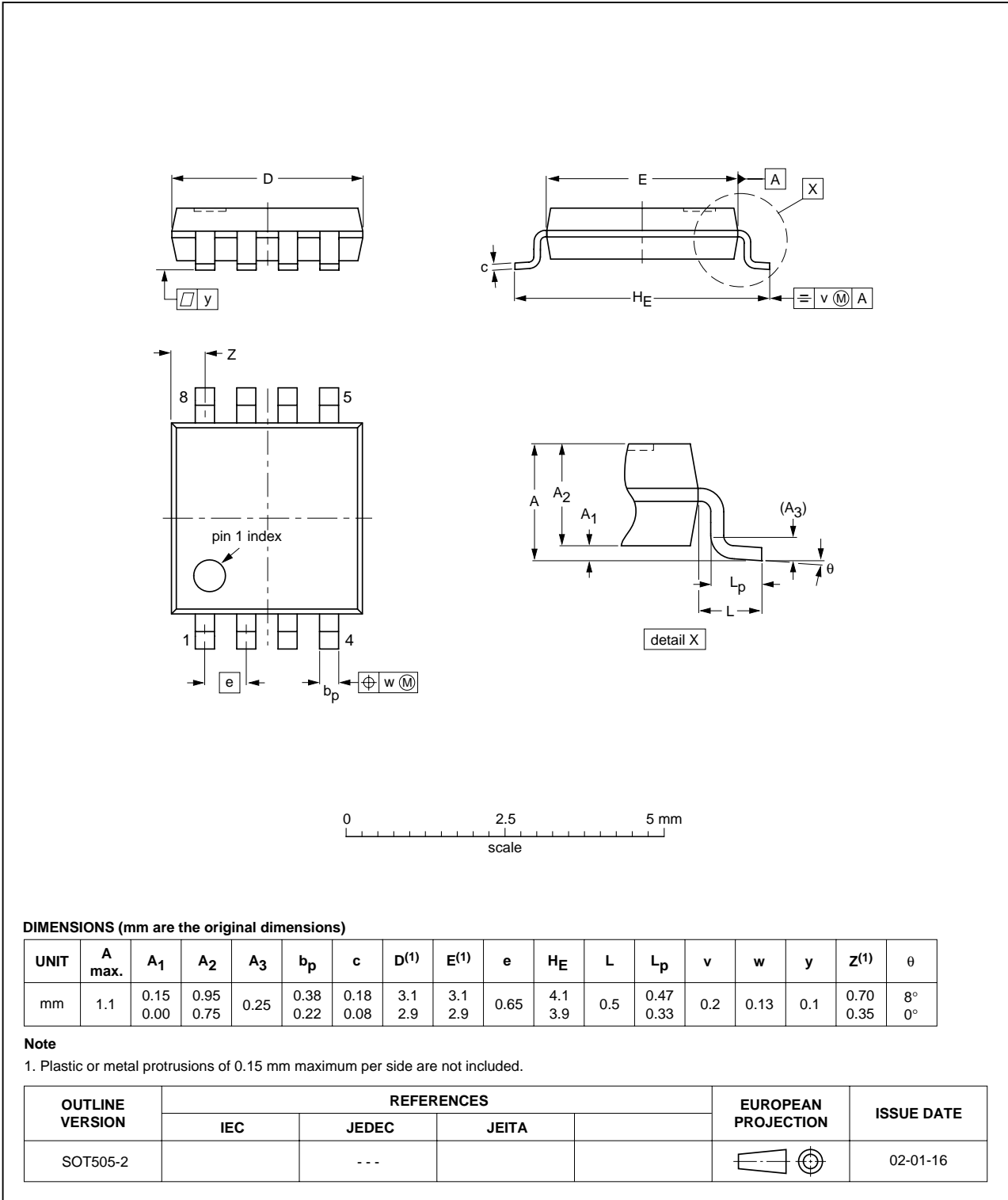


Fig 8. Package outline SOT505-2 (TSSOP8)



VSSOP8: plastic very thin shrink small outline package; 8 leads; body width 2.3 mm

SOT765-1

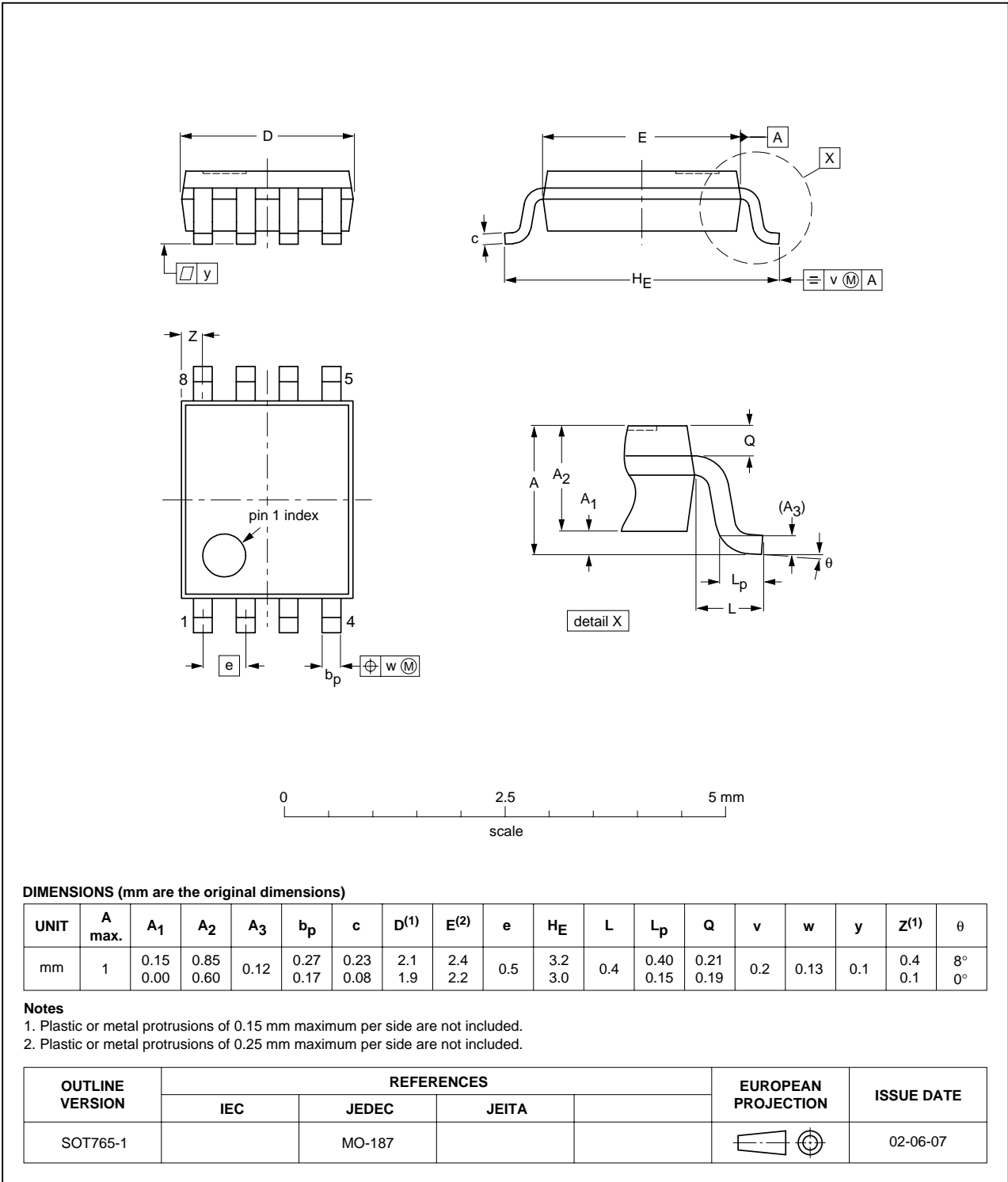


Fig 9. Package outline SOT765-1 (VSSOP8)

XSON8U: plastic extremely thin small outline package; no leads;  
8 terminals; UTLP based; body 3 x 2 x 0.5 mm

SOT996-2

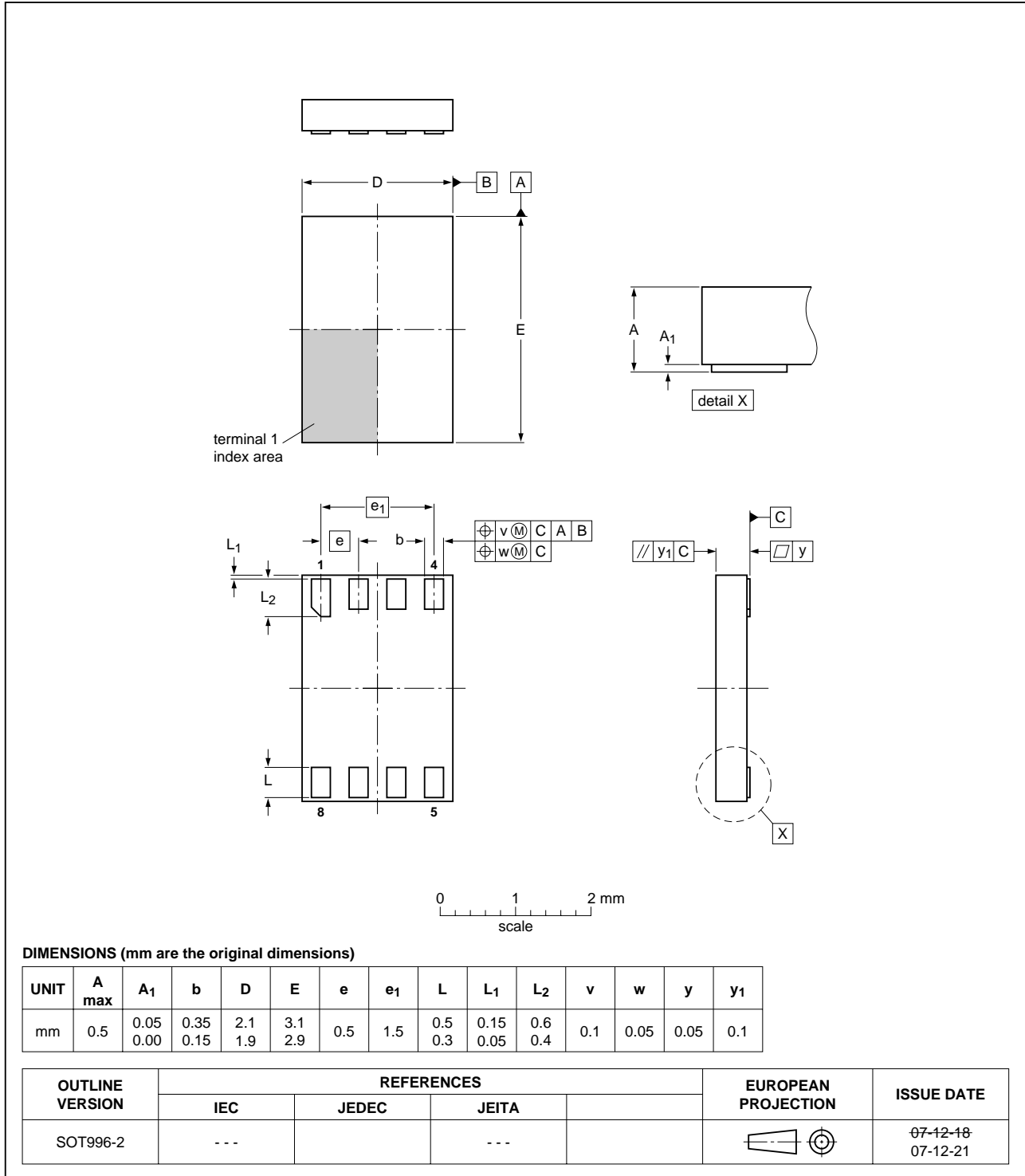


Fig 10. Package outline SOT996-2 (XSON8U)

## 14. Abbreviations

Table 11. Abbreviations

Acronym	Description
CMOS	Complementary Metal-Oxide Semiconductor
DUT	Device Under Test
ESD	ElectroStatic Discharge
HBM	Human Body Model
MM	Machine Model
TTL	Transistor-Transistor Logic

## 15. Revision history

Table 12. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
74HC_HCT3G04_3	20080702	Product data sheet	-	74HC_HCT3G04_2
Modifications:	<ul style="list-style-type: none"> <li>The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li> <li>Legal texts have been adapted to the new company name where appropriate.</li> <li>Added type number 74HC3G04GD and 74HCT3G04GD (XSON8U package).</li> </ul>			
74HC_HCT3G04_2	20031030	Product specification	-	74HC_HCT3G04_1
74HC_HCT3G04_1	20020726	Product specification	-	-

## 16. Legal information

### 16.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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## **О компании**

ООО "ТрейдЭлектроникс" - это оперативные поставки широкого спектра электронных компонентов отечественного и импортного производства напрямую от производителей и с крупнейших мировых складов. Реализуемая нашей компанией продукция насчитывает более полумиллиона наименований.

Благодаря этому наша компания предлагает к поставке практически не ограниченный ассортимент компонентов как оптовыми, мелкооптовыми партиями, так и в розницу.

Наличие собственной эффективной системы логистики обеспечивает надежную поставку продукции по конкурентным ценам в точно указанные сроки.

Срок поставки со стоков в **Европе и Америке – от 3 до 14 дней.**

Срок поставки из **Азии – от 10 дней.**

Благодаря развитой сети поставщиков, помогаем в поиске и приобретении экзотичных или снятых с производства компонентов.

Предоставляем спец цены на элементы для создания инженерных сэмплов.

**Упорный труд, качественный результат дают нам право быть уверенными в себе и надежными для наших клиентов.**

### **Наша компания это:**

- Гарантия качества поставляемой продукции
- Широкий ассортимент
- Минимальные сроки поставок
- Техническая поддержка
- Подбор комплектации
- Индивидуальный подход
- Гибкое ценообразование

Наша организация особенно сильна в поставках модулей, микросхем, пассивных компонентов, ксайленсах (XC), EPF, EPM и силовой электроники.

Большой выбор предлагаемой продукции, различные виды оплаты и доставки, позволят Вам сэкономить время и получить максимум выгоды от сотрудничества с нами!

## Перечень производителей, продукцию которых мы поставляем на российский рынок



С удовольствием будем прорабатывать для Вас поставки всех необходимых компонентов по текущим запросам для скорейшего выявления групп элементов, по которым сотрудничество именно с нашей компанией будет для Вас максимально выгодным!

С уважением,

Менеджер отдела продаж ООО

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